

High-efficiency normal-incidence vertical p-i-n photodetectors on a germanium-on-insulator platform: publisher's note

YIDING LIN,^{1,2,4} KWANG HONG LEE,² SHUYU BAO,^{1,2} XIN GUO,¹ HONG WANG,¹ JURGEN MICHEL,^{2,3} AND CHUAN SENG TAN^{1,2,*}

¹School of Electrical and Electronic Engineering, Nanyang Technological University, Singapore 639798, Singapore

²Low Energy Electronic Systems (LEES), Singapore-MIT Alliance for Research and Technology, Singapore 138602, Singapore

³Department of Materials Science and Engineering, Massachusetts Institute of Technology, Cambridge, Massachusetts 02139, USA

⁴e-mail: liny0075@e.ntu.edu.sg

*Corresponding author: tancs@ntu.edu.sg

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This publisher's note reports corrections to Eq. (1) in [Photon. Res. 5, 702 (2017)]. © 2017 Chinese Laser Press

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Equation (1) was corrected in the article [1] from

$$I_{\text{dark}} = BT^{1.5} e^{-\frac{E_g}{kT}} \{ \exp[qV/(e2kT)] - 1 \}$$

to

$$I_{\text{dark}} = BT^{1.5} e^{-\frac{E_g}{kT}} \left(e^{\frac{qV}{2kT}} - 1 \right)$$

The article [1] was corrected online as of 27 November 2017.

REFERENCE

1. Y. Lin, K. H. Lee, S. Bao, X. Guo, H. Wang, J. Michel, and C. S. Tan, "High-efficiency normal-incidence vertical p-i-n photodetectors on a germanium-on-insulator platform," *Photon. Res.* 5(6), 702–709 (2017).